

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in this application:

LISTING OF CLAIMS:

Claims 1 to 15. (Canceled).

16. (Currently Amended) A layer system, comprising:
an ~~etching~~ etched layer, whereby the ~~etching~~ etched layer is a silicon layer;
and
a passivation layer applied at least regionally to a surface of the silicon layer,
wherein:
the passivation layer includes a first, at least largely, inorganic partial layer and a second partial layer, and
the second partial layer is made of an organic compound.

17. (Previously Presented) The layer system as recited in Claim 16, wherein the organic compound contains a halogen.

18. (Previously Presented) The layer system as recited in Claim 16, wherein:
the organic compound includes a silane corresponding to one of an organic fluorine silane, an organic fluorochlorine silane, and a siloxane.

19. (Currently Amended) ~~The~~ A layer system ~~as recited in Claim 16,~~
comprising:
an etched layer, whereby the etched layer is a silicon layer; and
a passivation layer applied at least regionally to a surface of the silicon layer,
wherein:
the passivation layer includes a first, at least largely, inorganic partial layer and a second partial layer, and
the second partial layer is made of an organic compound,
wherein the organic compound has the general formula $R_a-R_b-Si(X)_{3-n}-(R_c)_n$,
 R_a being a perfluorinated polyether or a perfluorinated alkyl group having 1 to 16

carbon atoms, especially 6 to 12 carbon atoms, R_b and R_c being an alkyl group, and X being a halogen, an acetoxy group or an alkoxyl group, and n having a value of 0 to 2.

20. (Currently Amended) The layer system as recited in Claim 16, wherein the first partial layer is at least largely composed of an oxide layer ~~including~~ having a silicon oxide.

21. (Previously Presented) The layer system as recited in Claim 16, wherein the first partial layer has a thickness of 1 nm to 100 nm.

22. (Previously Presented) The layer system as recited in Claim 16, wherein the first partial layer has a thickness of 1nm to 20 nm.

23. (Previously Presented) The layer system as recited in Claim 16, wherein the first partial layer is directly applied one of (a) to the silicon layer and (b) on a layer of silicon oxide situated on the silicon layer.

24. (Previously Presented) The layer system as recited in one Claim 16, wherein the second partial layer is a self-assembled monolayer.

25. (Previously Presented) The layer system as recited in Claim 16, wherein the second partial layer has a thickness of 0.5 nm to 30 nm.

26. (Previously Presented) The layer system as recited in Claim 16, wherein the second partial layer has a thickness of 5 nm to 20 nm.

27. (Previously Presented) The layer system as recited in Claim 16, wherein the passivation layer protects the silicon layer with respect to an etch attack by a gaseous halogen fluoride including one of ClF_3 and BrF_3 .

28. (Previously Presented) The layer system as recited in Claim 16, wherein the passivation layer is free of micro-scale or nano-scale channels which are permeable for a gas including one of ClF_3 , BrF_3 and a vapor.